

2SC1623

Silicon PNP Epitaxial Type Transistor

Features

- High DC current gain: $h_{FE}=200$ TYP

($V_{CE}=6.0V, I_C=1.0mA$).

- High Voltage: $V_{CEO}=50V$
- RoHS compliant package

Applications

NPN Silicon Epitaxial Planar Transistor.

Audio frequency general purpose amplifier.

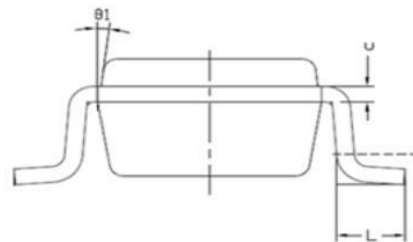
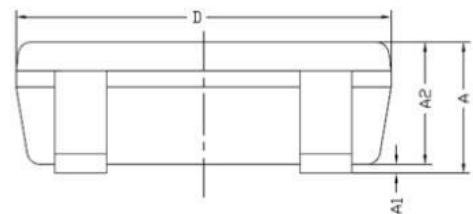
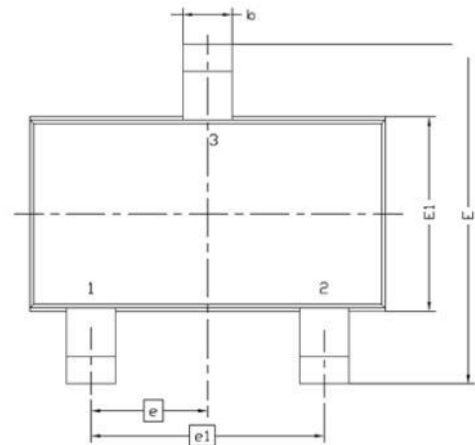
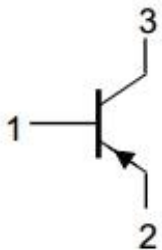
Packing & Order Information

3,000/Reel



**RoHS
COMPLIANT**

Graphic symbol



Symbol	MILLIMETERS	
	MIN	MAX
A	0.8	1.2
A1	0	0.1
A2	0.7	1.1
b	0.3	0.5
c	0.1	0.2
D	2.7	3.1
E	2.6	3
E1	1.4	1.8
e	0.95 BSC	
e1	1.9 BSC	
L	0.3	0.6
θ1	7° NOM	

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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	100	mA
P _C	Collector Dissipation	200	mW
T _J , T _{stg}	Junction and Storage Temperature	-55 to +150	°C

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Symbol	Parameter	Test Conditions	MIN	TYP	MAX	UNIT
V _{(BR)CBO}	Collector-base breakdown voltage	I _C = 100μA , I _E = 0	60			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = 1mA , I _B = 0	50			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E = 100μA , I _C = 0	5			V
I _{CBO}	Collector cut-off current	V _{CB} = 60 V , I _E = 0				μA
I _{EBO}	Emitter cut-off current	V _{EB} = 5 V , I _C = 0				μA
h _{FE}	DC current gain	V _{CE} = 6 V , I _C = 1 mA	90	200	600	
V _{CE(sat)}	Collector-emitter saturation voltage	I _C = 100mA , I _B = 10mA		0.15	0.3	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C = 100mA , I _B = 10mA		0.86	1.0	V
V _{BE}	Base Emitter Voltage	V _{CE} = 6 V , I _C = 1 mA	0.55	0.62	0.65	V
f _T	Transition frequency	V _{CE} = 6 V , I _E = -10 mA		250		MHz
C _{ob}	Output capacitance	V _{CB} = 6 V , I _E = 0 f = 1.0MHz		3.0		pF

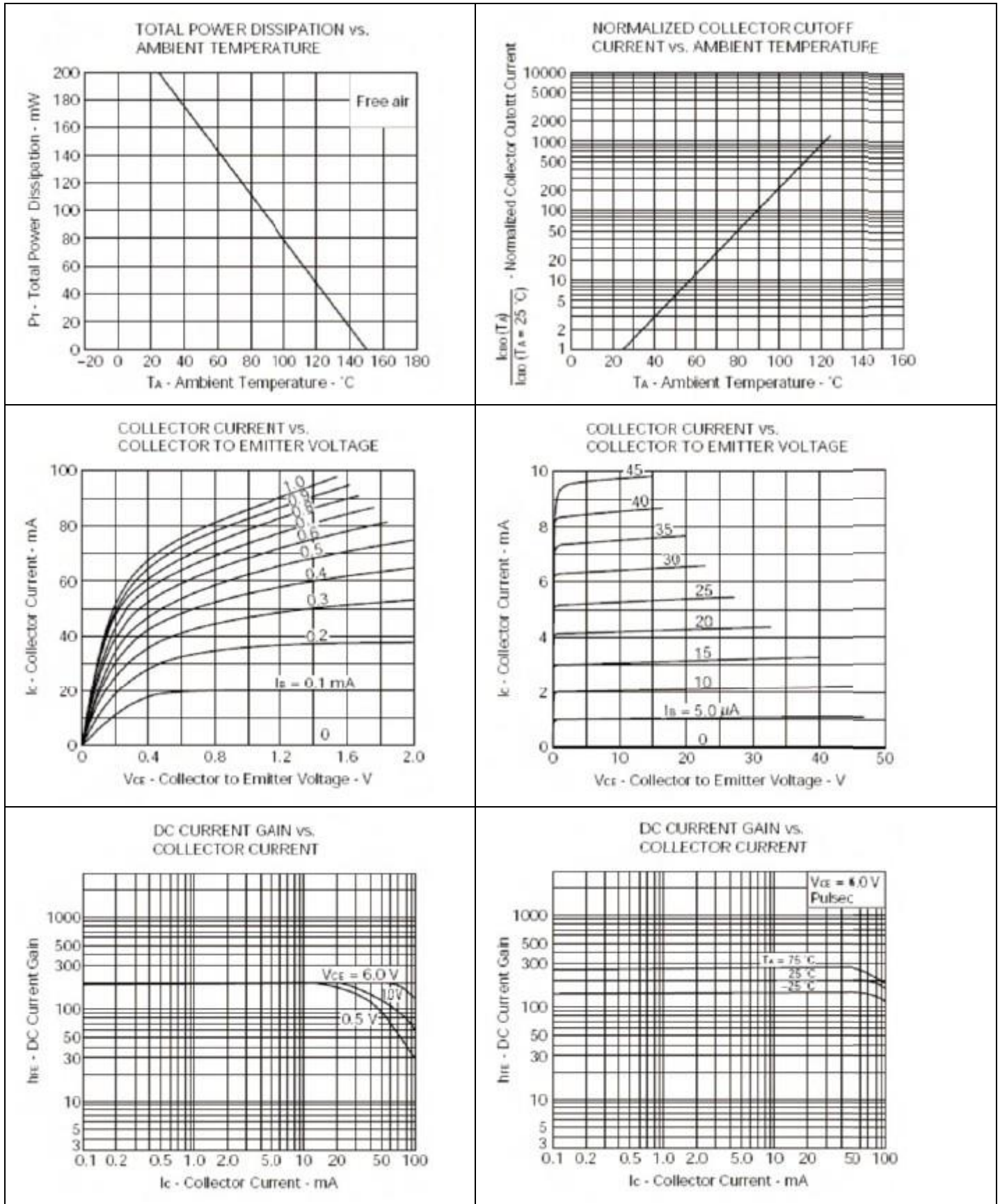
CLASSIFICATION OF h_{FE}(1)

Rank	L4	L5	L6	L7
Range	90-180	135-270	200-400	300-600
Marking	L4	L5	L6	L7

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■ RATINGS AND CHARACTERISTIC CURVES



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